a current generator having a first resistance, and

a circuit connected to said current generator and to said capacitance comprising a second resistance and enabling a capacitance charging current to be proportional to a square of a ratio of the second resistance and the first resistance.

10. A voltage ramp generator according to Claim 9, wherein said charging circuit comprises a degenerate current mirror circuit.

11. A voltage ramp generator according to Claim 10, wherein said degenerate current mirror circuit comprises:

a first MOS transistor having a channel of a first conductivity type comprising a gate, a drain and a source, the drain and the gate being connected to said current generator, and the source being connected to said second resistance; and

a second MOS transistor having a channel of the first conductivity type comprising a gate, a drain and a source, the gate being connected to the gate of said first MOS transistor, the source being connected to a supply voltage, and the drain being connected to said capacitance.

12. A voltage ramp generator according to Claim 11, wherein each of said first and second MOS transistors comprises a P-channel MOS transistor.

13. A voltage ramp generator according to Claim 9, wherein said capacitance comprises a gate capacitance of a MOS transistor.

14. A voltage ramp generator according to Claim 9, wherein current generated by said current generator is based upon the equation:

$$Ig2 = K2 \times \frac{Vg2}{Rg2}$$

where Ig2 is the current, K2 is a proportionality coefficient, Rg2 is the first resistance, and Vg2 is a reference voltage proportional to the quantity $k\frac{T}{q}$, where k is the Boltzmann constant, T is absolute temperature, and q is the charge of an electron.

15. A voltage ramp generator comprising:

a capacitance; and

a charging circuit connected to said capacitance and comprising

a current generator, and

a degenerate current mirror circuit connected to said current generator and to said capacitance for generating a capacitance charging current.

16. A voltage ramp generator according to Claim 15, wherein said current generator has a first resistance, and said degenerate current mirror circuit has a second resistance such that the capacitance charging current is proportional to a square of a ratio of the second resistance and the first resistance.

17. A voltage ramp generator according to Claim 15, wherein said degenerate current mirror circuit comprises:

a first MOS transistor having a channel of a first conductivity type comprising a gate, a drain and a source, the drain and the gate being connected to said current generator, and the source being connected to said second resistance; and

a second MOS transistor having a channel of the first conductivity type comprising a gate, a drain and a source, the gate being connected to the gate of said first MOS transistor, the source being connected to a supply voltage, and the drain being connected to said capacitance.

18. A voltage ramp generator according to Claim 17, wherein each of said first and second MOS transistors comprises a P-channel MOS transistor.

19. A voltage ramp generator according to Claim 15, wherein said capacitance comprises a gate capacitance of a MOS transistor.

20. A voltage ramp generator according to Claim 15, wherein current generated by said current generator is based upon the equation:

$$Ig2 = K2 \times \frac{Vg2}{Rg2}$$

where Ig2 is the current, K2 is a proportionality coefficient, Rg2 is the first resistance, and Vg2 is a reference voltage proportional to the quantity $k\frac{T}{q}$, where k is

the Boltzmann constant, T is absolute temperature, and q is the charge of an electron.

21. A current ramp generator comprising:

a voltage ramp generator comprising

a capacitance, and

a charging circuit connected to said capacitance and comprising

a current generator having a first resistance, and

a circuit connected to said current generator and to said capacitance comprising a second resistance and enabling a capacitance charging current to be proportional to a square of a ratio of the second resistance and the first resistance; and

a conversion circuit connected to said voltage ramp generator for generating a current ramp.

22. A current ramp generator according to Claim 21, wherein said conversion circuit comprises a third resistance.

23. A current ramp generator according to Claim 21, wherein said third resistance comprises an implanted resistance having a positive temperature coefficient.

24. A current ramp generator according to Claim 21, wherein said charging circuit comprises a degenerate current mirror circuit.

25. A current ramp generator according to Claim 24, wherein said degenerate current mirror circuit comprises:

a first MOS transistor having a channel of a first conductivity type comprising a gate, a drain and a source, the drain and the gate being connected to said current generator, and the source being connected to said second resistance; and

a second MOS transistor having a channel of the first conductivity type comprising a gate, a drain and a source, the gate being connected to the gate of said first MOS transistor, the source being connected to a supply voltage, and the drain being connected to said capacitance.

26. A current ramp generator according to Claim 25, wherein each of said first and second MOS transistors comprises a P-channel MOS transistor.

27. A current ramp generator according to Claim 21, wherein said capacitance comprises a gate capacitance of a MOS transistor.

28. A current ramp generator according to Claim 21, wherein current generated by said current generator is based upon the equation:

$$Ig2 = K2 \times \frac{Vg2}{Rg2}$$

where Ig2 is the current, K2 is a proportionality coefficient, Rg2 is the first resistance, and Vg2 is a reference voltage proportional to the quantity $k\frac{T}{q}$, where k is the Boltzmann constant, T is absolute temperature, and q is the charge of an electron.

29. A current ramp generator comprising:

a voltage ramp generator comprising

a capacitance, and

a charging circuit connected to said capacitance and comprising

a current generator, and

a degenerate current mirror circuit connected to said current generator and to said capacitance for generating a capacitance charging current; and

a third resistance connected to said voltage ramp generator for generating a current ramp.

30. A current ramp generator according to Claim 29, wherein said current generator has a first resistance, and said degenerate current mirror circuit has a second resistance such that the capacitance charging current is proportional to a square of a ratio of the second resistance and the first resistance.

31. A current ramp generator according to Claim 29, wherein said third resistance comprises an implanted resistance having a positive temperature coefficient.

32. A current ramp generator according to Claim 29, wherein said degenerate current mirror circuit comprises:

a first MOS transistor having a channel of a first conductivity type comprising a gate, a drain and a source, the drain and the gate being connected to said current generator, and the source being connected to said second resistance; and

a second MOS transistor having a channel of the first conductivity type comprising a gate, a drain and a

source, the gate being connected to the gate of said first MOS transistor, the source being connected to a supply voltage, and the drain being connected to said capacitance.

33. A current ramp generator according to Claim 32, wherein each of said first and second MOS transistors comprises a P-channel MOS transistor.

34. A current ramp generator according to Claim 29, wherein said capacitance comprises a gate capacitance of a MOS transistor.

35. A current ramp generator according to Claim 29, wherein current generated by said current generator is based upon the equation:

$$Ig2 = K2 \times \frac{Vg2}{Rg2}$$

where Ig2 is the current, K2 is a proportionality coefficient, Rg2 is the first resistance, and Vg2 is a reference voltage proportional to the quantity $k\frac{T}{q}$, where k is the Boltzmann constant, T is absolute temperature, and q is the charge of an electron.

36. A method for generating a ramp voltage comprising the steps of:

generating a capacitance charging current using a charging circuit comprising a current generator having a first resistance and a circuit connected to the generator comprising

a second resistance for enabling the capacitance charging current to be proportional to a square of a ratio of the second resistance and the first resistance; and

charging a capacitance with the capacitance charging current for generating the ramp voltage.

37. A method according to Claim 36, wherein the circuit comprises a degenerate current mirror circuit.

38. A method according to Claim 37, wherein the degenerate current mirror circuit comprises:

a first MOS transistor having a channel of a first conductivity type comprising a gate, a drain and a source, the drain and the gate being connected to said current generator, and the source being connected to said second resistance; and

a second MOS transistor having a channel of the first conductivity type comprising a gate, a drain and a source, the gate being connected to the gate of said first MOS transistor, the source being connected to a supply voltage, and the drain being connected to said capacitance.

39. A method according to Claim 36, wherein the capacitance comprises a gate capacitance of a MOS transistor.

40. A method according to Claim 36, wherein current generated by the current generator is based upon the equation:

$$Ig2 = K2 \times \frac{Vg2}{Rg2}$$

where Ig2 is the current, K2 is a proportionality coefficient, Rg2 is the first resistance, and Vg2 is a